

GaAs PIN photodiode with preamp G9285-14

ROSA type, 850 nm, 1.25 Gbps



Features

- $\phi 1.25$ mm sleeve type ROSA (Receiver Optical Sub-Assembly)
- High-speed response: 1.25 Gbps
- High gain with AGC (Auto Gain Control): 2.0 V/mW (-20 dBm)
- Low power supply voltage: 3.3 V, 5 V
- Differential output
- Sensitivity: 0 to -25 dBm Typ.

Applications

- Gigabit Ethernet
- Fiber channel

■ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Supply voltage	Vcc	-0.3, +5.5	V
Operating temperature	Topr	-20 to +70 *1	°C
Storage temperature	Tstg	-40 to +85 *1	°C

*1: No condensation

■ Electrical and optical characteristics

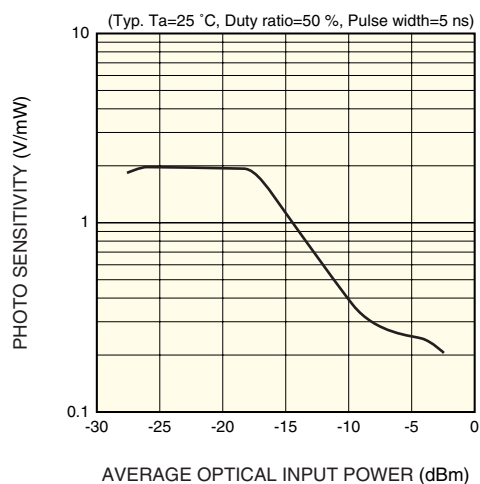
(Ta=25 °C, Vcc=3.3 V or 5 V, Vee=GND, RL=50 Ω *2, λ =850 nm, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Photo sensitivity *2, *3	S	Pin= -20 dBm *3 (f=100 MHz)	1.4	2.0	-	V/mW
Supply current	Icc	Dark state, RL= ∞	-	35	41	mA
Output bias voltage	Vo	Dark state, RL= ∞	Vcc=3.3 V	1.6	-	V
			Vcc=5.0 V	3.3	-	
Cut-off frequency *2, *3	fc	-3 dB (0 dB at 100 MHz)	-	1000	-	MHz
Low cut-off frequency *2	fc-L	Pin= -20 dBm, -3 dB	-	DC	-	kHz
Noise equivalent power *2, *3	NEP	Dark state, to 938 MHz	-	450	-	nWrms
Minimum receivable sensitivity	Pmin	1.25 Gbps, NRZ, PN=23, BER=10 ⁻¹² , Extinction ratio=9 dB	-	-25	-	dBm
Maximum receivable sensitivity	Pmax		-	0	-	

*2: Output: Capacitive coupling

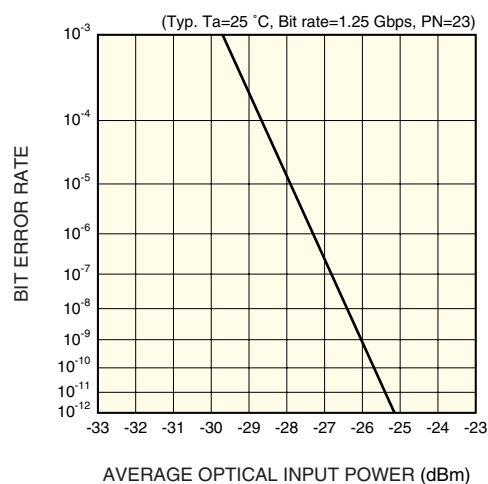
*3: Single-ended (Vout+) measurement

■ Photo sensitivity vs. average optical input power



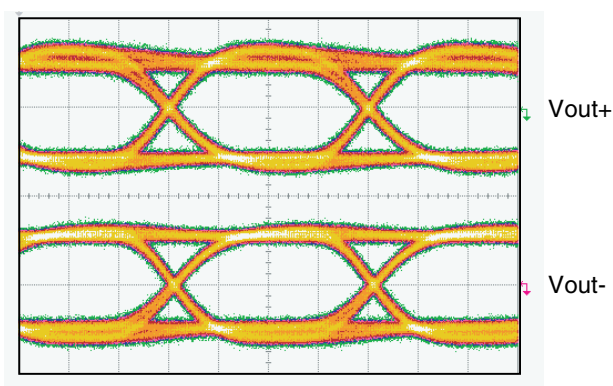
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■ Bit error rate

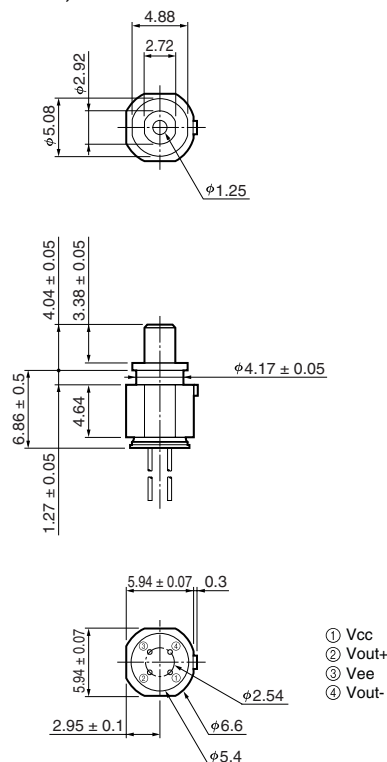


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■ Eye diagram



Bit rate=1.25 Gbps, PN=23
 $\lambda=850\text{ nm}$, $P_{in}=-20\text{ dBm}$, $V_{cc}=3.3\text{ V}$

■ Dimensional outline
(unit: mm, unless otherwise noted: ± 0.15)

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Cat. No. KGPD1010E02
Apr. 2003 DN